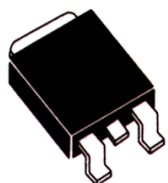




CJD200 NPN
CJD210 PNP

COMPLEMENTARY SILICON
POWER TRANSISTOR

DDPAK POWER!™



DDPAK CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD200, CJD210 types are Complementary Silicon Power Transistors manufactured in a surface mount package designed for high current amplifier applications.

MAXIMUM RATINGS ($T_C=25^\circ\text{C}$)

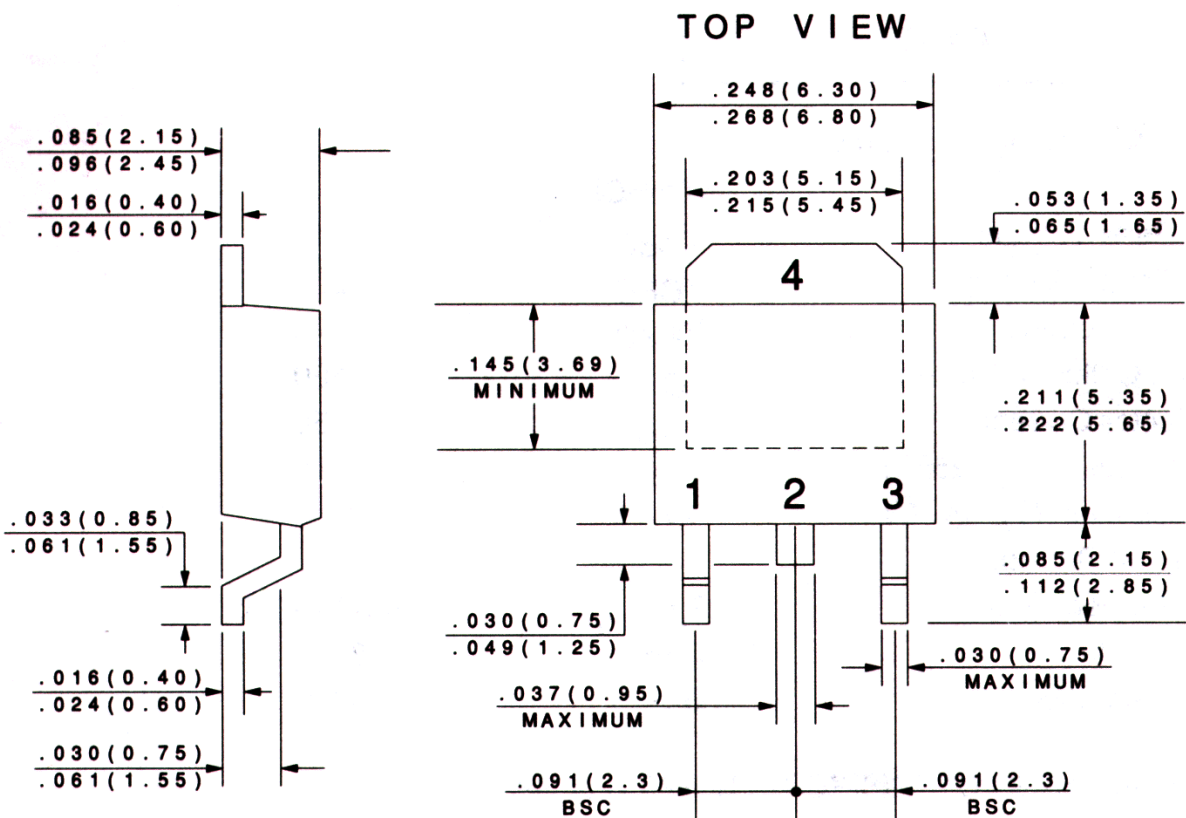
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	8.0	V
Continuous Collector Current	I_C	5.0	A
Peak Collector Current	I_{CM}	10	A
Base Current	I_B	1.0	A
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	12.5	W
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	1.4	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JC}	10	$^\circ\text{C/W}$
Thermal Resistance	θ_{JA}	89.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=40\text{V}$		100	nA
I_{CBO}	$V_{CB}=40\text{V}, T_C=125^\circ\text{C}$		100	μA
I_{EBO}	$V_{EB}=8.0\text{V}$		100	nA
BV_{CEO}	$I_C=10\text{mA}$	25		V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$		0.75	V
$V_{CE(SAT)}$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		1.8	V
$V_{BE(SAT)}$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		2.5	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=2.0\text{A}$		1.6	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	70		

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=1.0V, I_C=2.0A$	45	180	
h_{FE}	$V_{CE}=2.0V, I_C=5.0A$	10		
f_T	$V_{CE}=10V, I_C=100mA, f=10MHz$	65		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=0.1MHz$ (CJD200)		80	pF
C_{ob}	$V_{CB}=10V, I_E=0, f=0.1MHz$ (CJD210)		120	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR